

MOTOROLA

SEMICONDUCTOR TECHNICAL DATA

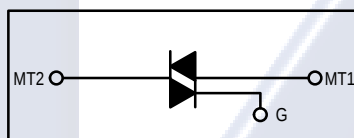
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by MAC223FP/D

Triacs

Silicon Bidirectional Triode Thyristors

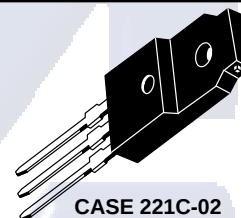
... designed primarily for full-wave ac control applications, such as lighting systems, heater controls, motor controls and power supplies; or wherever full-wave silicon-gate-controlled devices are needed.

- Off-State Voltages to 800 Volts
- All Diffused and Glass Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Thermal Resistance and High Heat Dissipation
- Gate Triggering Guaranteed in Three Modes (MAC223FP Series) or Four Modes (MAC223AFP Series)



MAC223FP Series MAC223AFP Series

**ISOLATED TRIACs
THYRISTORS
25 AMPERES RMS
200 thru 800 VOLTS**



MAXIMUM RATINGS ($T_J = 25^\circ$ unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage ⁽¹⁾ ($T_J = -40$ to $+125^\circ\text{C}$, 1/2 Sine Wave 50 to 60 Hz, Gate Open)	V_{DRM}	200 400 600 800	Volts
On-State RMS Current ($T_C = +80^\circ\text{C}$) Full Cycle Sine Wave 50 to 60 Hz ⁽²⁾	$I_T(\text{RMS})$	25	Amps
Peak Nonrepetitive Surge Current (One Full Cycle, 60 Hz, $T_C = 80^\circ\text{C}$, preceded and followed by rated current)	I_{TSM}	250	Amps
Circuit Fusing ($t = 8.3$ ms)	I^2t	260	A^2s
Peak Gate Power ($t \leq 2$ μs)	P_{GM}	20	Watts
Average Gate Power ($T_C = +80^\circ\text{C}$, $t \leq 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
Peak Gate Current ($t \leq 2$ μs)	I_{GM}	2	Amps
Peak Gate Voltage ($t \leq 2$ μs)	V_{GM}	± 10	Volts
RMS Isolation Voltage ($T_A = 25^\circ\text{C}$, Relative Humidity $\leq 20\%$)	$V_{(ISO)}$	1500	Volts
Operating Junction Temperature	T_J	-40 to $+125$	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$
Mounting Torque	—	8	in. lb.

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.

THERMAL CHARACTERISTICS

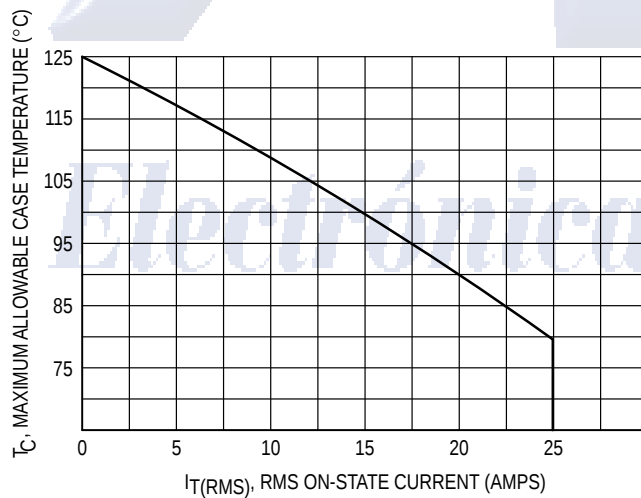
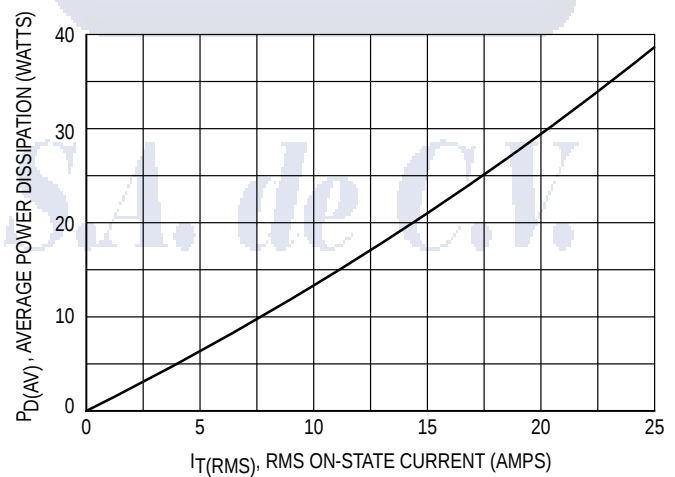
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	$^\circ\text{C}/\text{W}$
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^\circ\text{C}/\text{W}$



MAC223FP Series MAC223AFP Series**ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$ and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current ⁽¹⁾ ($V_D = \text{Rated } V_{\text{DRM}}$, Gate Open)	I_{DRM}	— —	— —	10 2	μA mA
Peak On-State Voltage ($I_{\text{TM}} = 35\text{ A Peak}$, Pulse Width $\leq 2\text{ ms}$, Duty Cycle $\leq 2\%$)	V_{TM}	—	1.4	1.85	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12\text{ V}$, $R_L = 100\ \Omega$) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY	I_{GT}	— —	20 30	50 75	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12\text{ V}$, $R_L = 100\ \Omega$) MT2(+), G(+); MT2(-), G(-); MT(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY ($V_D = \text{Rated } V_{\text{DRM}}$, $T_J = 125^\circ\text{C}$, $R_L = 10\text{ k}$) MT(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY	V_{GT}	— — 0.2 0.2	1.1 1.3 0.4 0.4	2 2.5 — —	Volts
Holding Current ($V_D = 12\text{ V}$, $I_{\text{TM}} = 200\text{ mA}$, Gate Open)	I_{H}	—	10	50	mA
Gate Controlled Turn-On Time ($V_D = \text{Rated } V_{\text{DRM}}$, $I_{\text{TM}} = 35\text{ A Peak}$, $I_{\text{G}} = 200\text{ mA}$)	t_{gt}	—	1.5	—	μs
Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{\text{DRM}}$, Exponential Waveform, $T_C = 125^\circ\text{C}$)	dv/dt	—	40	—	$\text{V}/\mu\text{s}$
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{\text{DRM}}$, $I_{\text{TM}} = 35\text{ A Peak}$, Commutating $di/dt = 12.6\text{ A/ms}$, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	—	5	—	$\text{V}/\mu\text{s}$

1. Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.

**Figure 1. RMS Current Derating****Figure 2. On-State Power Dissipation**

MAC223FP Series MAC223AFP Series

TYPICAL CHARACTERISTICS

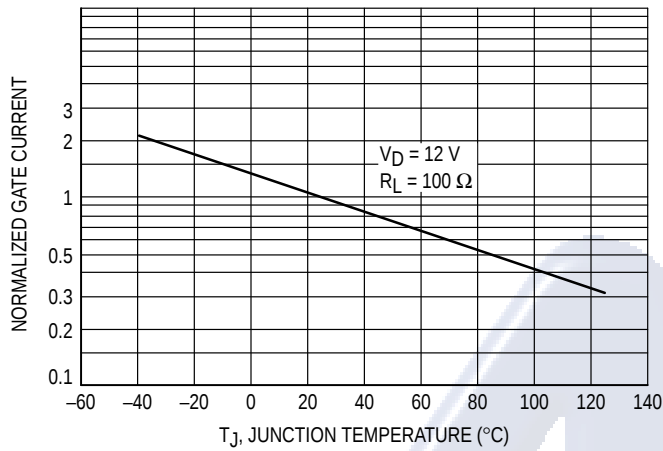


Figure 3. Gate Trigger Current

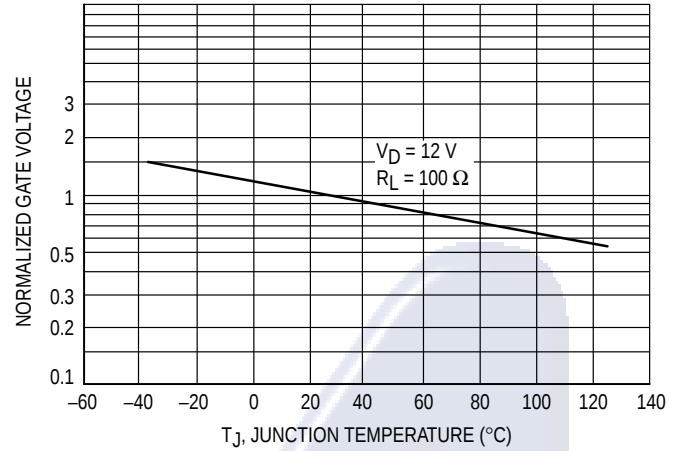


Figure 4. Gate Trigger Voltage

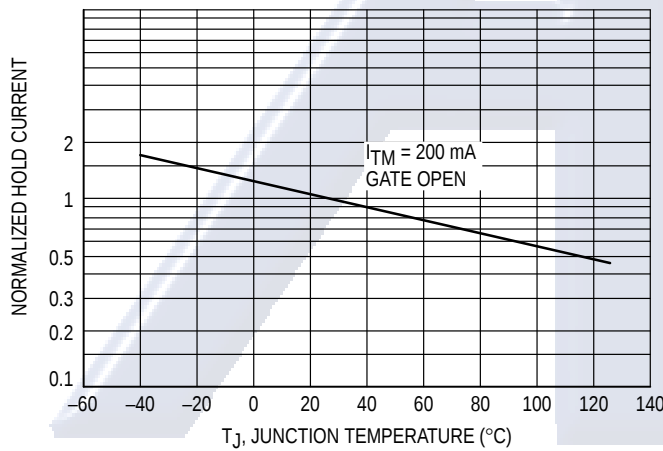


Figure 5. Hold Current

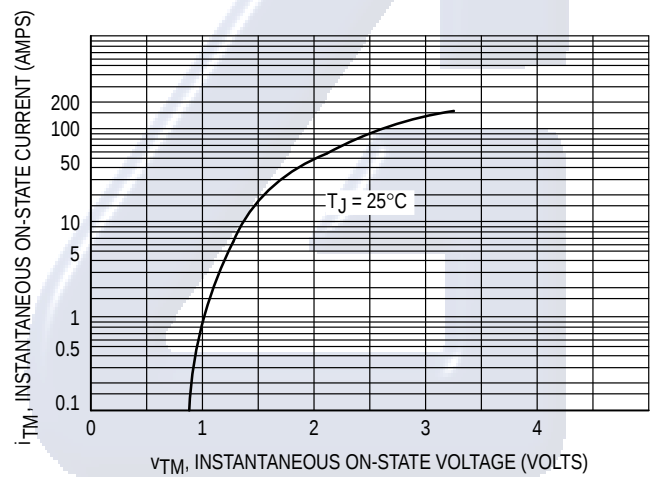
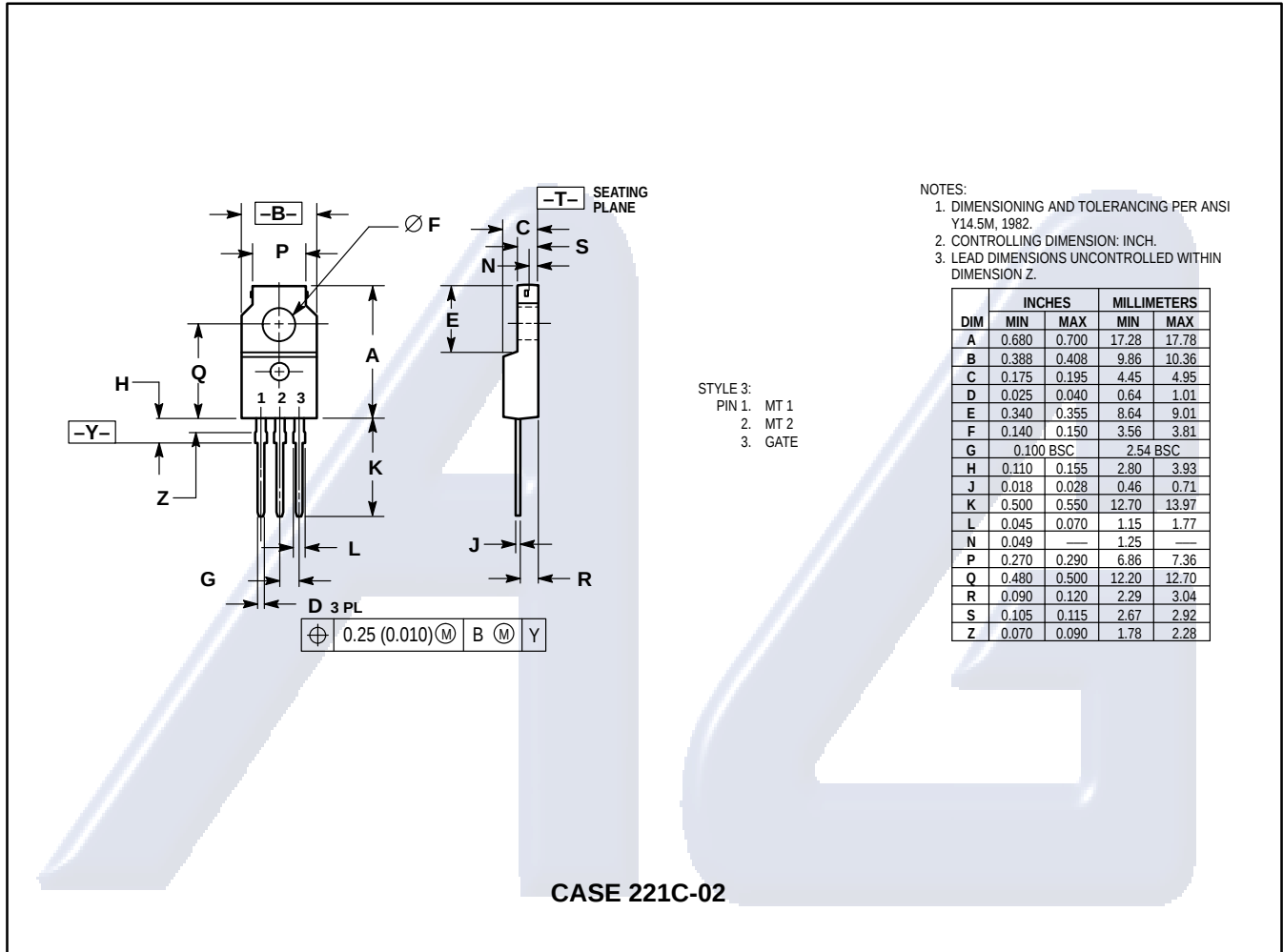


Figure 6. Typical On-State Characteristics

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MAC223FP Series MAC223AFP Series

PACKAGE DIMENSIONS



Electrónica S.A. de C.V.

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